

SI6433DQ-T1-E3-VB Datasheet

P-Channel 20-V (G-S) MOSFET

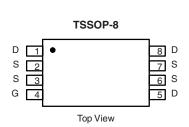
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
	0.010 at V _{GS} = - 4.5 V	- 9.0		
-20	0.012 at V _{GS} = - 2.5 V	- 7.8		
	0.016 at V _{GS} = - 1.8 V	- 6.0		

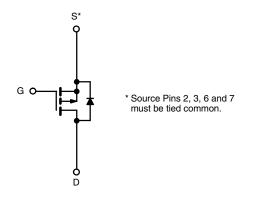
FEATURES

- Halogen-free
- Trench Power MOSFETs



COMPLIANT





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ C, unles			1	
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V _{GS}	± 12		V
Continuous Dunin Courset /T 450 90\d	T _A = 25 °C	I _D	- 9.0	-7.8	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 6.8	-5.8	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.35	- 0.95	
M ·	T _A = 25 °C	P _D	1.5	1.05	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.0	0.67	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian and Lunching to Ambient	t ≤ 10 s	R _{thJA}	65	83	
Maximum Junction-to-Ambient ^a	Steady State	' ¹thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	43	52	

Notes: a. Surface Mounted on 1" x 1" FR4 board.

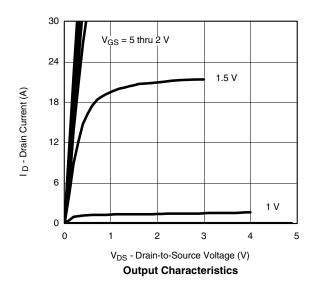


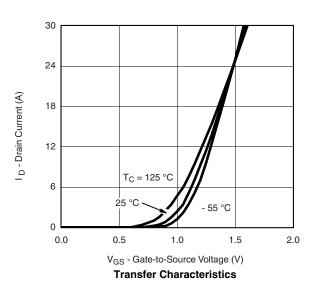
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -450 \mu A$	- 0.45	-	1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current		V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -20V$, $V_{GS} = 0$ V, $T_{J} = 70$ °C			- 25		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 20			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -8.0 \text{ A}$		0.010		Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -7.0 \text{ A}$		0.012			
		V _{GS} = - 1.8 V, I _D = - 5.8 A		0.016			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 8.0 A		44		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.5 A, V _{GS} = 0 V		- 0.56	- 1.1	٧	
Dynamic ^b							
Total Gate Charge	Q_g			46	70		
Gate-Source Charge	Q_{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 8.0 A		5		nC	
Gate-Drain Charge	Q_{gd}			15.5		1	
Turn-On Delay Time	t _{d(on)}			45	70		
Rise Time	t _r	V_{DD} = - 10 V, $R = 6 \Omega$		85	130		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 4.5 V, $R_g=$ 6 Ω		220	400	ns	
Fall Time	t _f			155	235		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.5 A, di/dt = 100 A/μs		140	210		

- Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

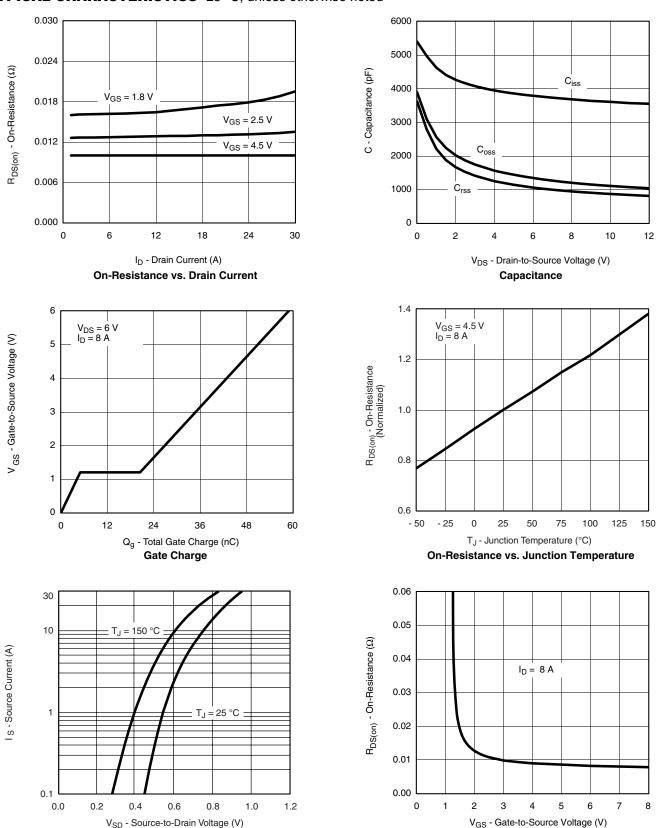
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







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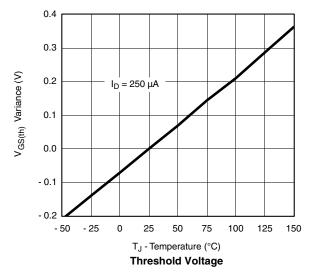


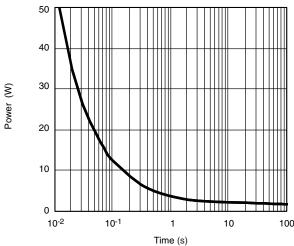
Source-Drain Diode Forward Voltage

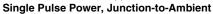
On-Resistance vs. Gate-to-Source Voltage

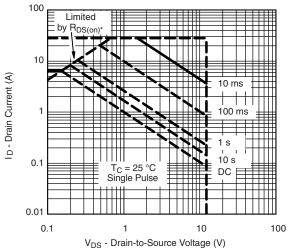


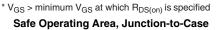
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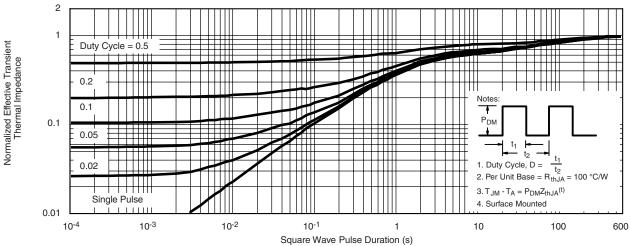








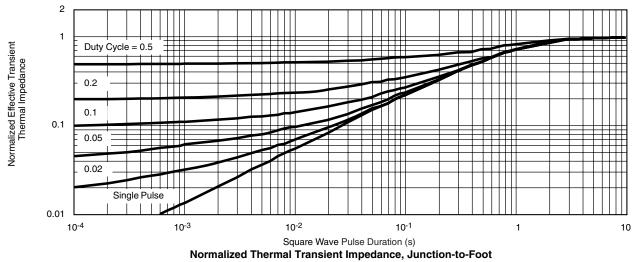




Normalized Thermal Transient Impedance, Junction-to-Ambient



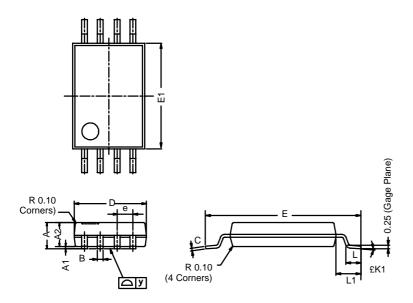
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TSSOP: 8-LEAD

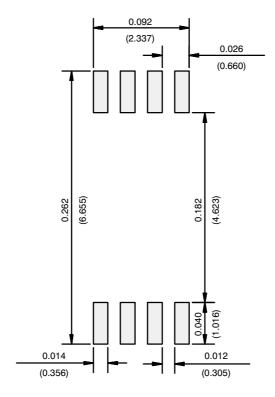
JEDEC Part Number: MO-153



	MILLIMETERS				
Dim	Min	Nom	Max		
Α	_	_	1.20		
A ₁	0.05	0.10	0.15		
A ₂	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
E	6.20	6.40	6.60		
E ₁	4.30	4.40	4.50		
е	-	0.65	-		
L	0.45	0.60	0.75		
L ₁	0.90	1.00	1.10		
Y	_	-	0.10		
£K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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